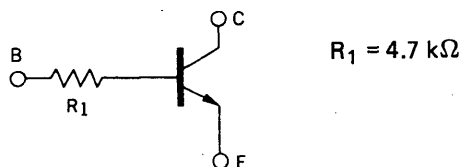


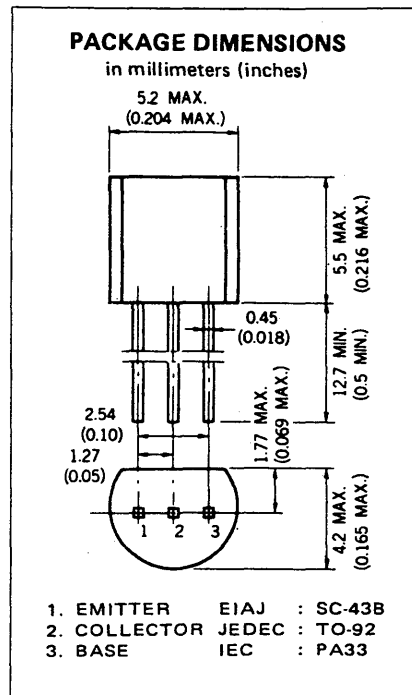
DESCRIPTION The AA1L3Z is designed for use in medium speed switching circuit.

FEATURE • Bias resistors built-in type NPN transistor equivalent circuit.



ABSOLUTE MAXIMUM RATINGS

- Maximum Temperatures
 - Storage Temperature -55 to $+150$ °C
 - Junction Temperature 150 °C Maximum
- Maximum Power Dissipation ($T_a = 25$ °C)
 - Total Power Dissipation 300 mW
- Maximum Voltages and Currents ($T_a = 25$ °C)
 - V_{CBO} Collector to Base Voltage 60 V
 - V_{CEO} Collector to Emitter Voltage 50 V
 - V_{EBO} Emitter to Base Voltage 5.0 V
 - $I_{C(DC)}$ Collector Current (DC) 100 mA
 - $I_{C(pulse)}$ Collector Current (pulse) 200 mA



ELECTRICAL CHARACTERISTICS ($T_a = 25$ °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
R_1	Input Resistance	3.29	4.7	6.11	k Ω	
V_{IL}	Low Level Input Voltage		0.54	0.5	V	$V_{CE} = 5.0$ V, $I_C = 100$ μ A
V_{IH}	Hi Level Input Voltage	1.2	0.71		V	$V_{CE} = 0.2$ V, $I_C = 5.0$ mA
t_{on}	Turn On Time		0.03	0.2	μ s	$V_{CC} = 5.0$ V, $R_L = 1.0$ k Ω , $V_{in} = 5.0$ V, PW = 2 μ s, Duty Cycle ≤ 2 %
t_{stg}	Storage Time		3.2	5.0	μ s	
t_{off}	Turn Off Time		3.4	6.0	μ s	
h_{FE1}	DC Current Gain	135	450	600	—	$V_{CE} = 5.0$ V, $I_C = 5.0$ mA
h_{FE2}	DC Current Gain	100	380		—	$V_{CE} = 5.0$ V, $I_C = 50$ mA
$V_{CE(sat)}$	Collector Saturation Voltage		0.04	0.2	V	$I_C = 5.0$ mA, $I_B = 0.25$ mA
I_{CBO}	Collector Cutoff Current			0.1	μ A	$V_{CB} = 50$ V, $I_E = 0$

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

